

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



2014年1月

FCI25N60N

N 沟道 SupreMOS[®] MOSFET 600 V, 25 A, 125 m Ω

特性

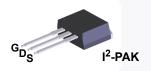
- $R_{DS(on)} = 107 \text{ m}\Omega \text{ (Typ.)}@V_{GS} = 10 \text{ V, } I_D = 12.5 \text{ A}$
- 超低栅极电荷 (典型值 Q_a = 57 nC)
- 低有效输出电容 (典型值 C_{oss(eff.)}= 262 pF)
- 100% 经过雪崩测试
- 符合 RoHS 标准

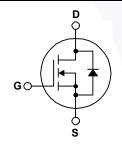
应用

- 太阳能逆变器
- · AC-DC 电源

说明

SupreMOS[®] MOSFET 是飞兆半导体的下一代高压超级结(SJ)技术,该技术采用区别于传统 SJ MOSFET 产品的深沟槽填充工艺。这项先进技术和精密的工艺控制提供了最低的 Rsp onresistance(导通电阻规格),卓越的开关性能和耐用性。SupreMOS MOSFET 产品非常适合高频开关电源转换器应用,如功率因数校正 (PFC)、服务器 / 电信电源、平板电视电源、ATX电源及工业电源应用。





MOSFET 最大额定值 T_C = 25°C 除非另有说明。

符号		参数		FCI25N60N_F102	单位	
V _{DSS}	漏极一源极电压			600	V	
V _{GSS}	栅极一源极电压			±30	V	
	足机力法	- 连续 (T _C = 25°C)		25	۸	
D	漏极电流	- 连续 (T _C = 100°C)		16	_ A	
DM	漏极电流	- 脉冲	(说明 1)	75	Α	
EAS	单脉冲雪崩能量		(说明 2)	861	mJ	
AR	雪崩电流		(说明 1)	8.3	Α	
E _{AR}	重复雪崩能量		(说明 1)	2.2	mJ	
dv/dt	MOSFET dv/dt			100	V/ns	
av/ut	二极管恢复 dv/dt 峰值		(说明 3)	15	V/115	
.	±±±¢	(T _C = 25°C)		216	W	
D	功耗	- 降低至 25°C 以上		1.72	W/°C	
Γ _J , T _{STG}	工作和存储温度范围			-55 至 +150	°C	
Γ _L	用于焊接的最大引线温度,	距离外壳 1/8",持续 5 秒		300	°C	

热性能

符号	参数	FCI25N60N_F102	单位
$R_{\theta JC}$	结至外壳热阻最大值	0.58	°C/W
$R_{\theta JA}$	结至环境热阻最大值	62.5	C/VV

封装标识与定购信息

器件编号	顶标	封装	包装方法	卷尺寸	带宽	数量
FCI25N60N_F102	FCI25N60N	I ² -PAK	塑料管	不适用	不适用	50 个

电气特性 T_C = 25°C 除非另有说明。

符号	参数	测试条件	最小值	典型值	最大值	单位
关断特性						
BV_DSS	漏极一源极击穿电压	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$	600	-	-	V
ΔBV _{DSS} / ΔT _J	击穿电压温度系数	I _D = 1 mA,参考温度为 25°C	-	0.74	-	V/°C
ı	泰柳林中区温林中 茨	V _{DS} = 480 V, V _{GS} = 0 V	-	-	10	^
DSS	零栅极电压漏极电流	$V_{DS} = 480 \text{ V}, T_{J} = 125^{\circ}\text{C}$	-	-	100	μΑ
I _{GSS}	栅极 - 体漏电流	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

导通特性

V _{GS(th)}	栅极阈值电压	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	V
R _{DS(on)}	漏极至源极静态导通电阻	V_{GS} = 10 V, I_{D} = 12.5 A	-	0.107	0.125	Ω
9 _{FS}	正向跨导	$V_{DS} = 20 \text{ V}, I_{D} = 12.5 \text{ A}$	-		-	S

动态特性

C _{iss}	输入电容	V = 400 V V = 0 V	-	2520	3352	pF
C _{oss}	输出电容	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz	-	103	137	pF
C _{rss}	反向传输电容	1 - 1 1/11/12	-	3.2	5	pF
C _{oss}	输出电容	$V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	55	-	pF
C _{oss(eff.)}	有效输出电容	$V_{DS} = 0 V \cong 480 V, V_{GS} = 0 V$	-	262	-	pF
Q _{g(tot)}	10 V 的栅极电荷总量	$V_{DS} = 380 \text{ V}, I_D = 12.5 \text{ A},$	-	57	74	nC
Q_{gs}	栅极 - 源极栅极电荷	V _{GS} = 10 V	-	10	-	nC
Q_{gd}	栅极 - 漏极 " 米勒 " 电荷	(说明 4)	-	18	-	nC
ESR	等效串联电阻 (G-S)	f = 1 MHz	-	1	-	Ω

开关特性

t _{d(on)}	导通延迟时间		- /	21	52	ns
t _r	开通上升时间	$V_{DD} = 380 \text{ V}, I_D = 12.5 \text{ A},$	-/	22	54	ns
t _{d(off)}	关断延迟时间	$V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	68	146	ns
t _f	关断下降时间	(说明 4)	/ -	5	20	ns

漏极 - 源极二极管特性

Is	漏极 - 源极二极管最大正向连续电流		-	-	25	Α
I _{SM}	漏极 - 源极二极管最大正向脉冲电流		-	-	75	Α
V_{SD}	漏极 - 源极二极管正向电压	$V_{GS} = 0 \text{ V}, I_{SD} = 12.5 \text{ A}$	-	-	1.2	V
t _{rr}	反向恢复时间	V _{GS} = 0 V, I _{SD} = 12.5 A,	-	370	-	ns
Q _{rr}	反向恢复电荷	$dI_F/dt = 100 A/\mu s$	-	7	-	μС

- 1. 重复额定值: 脉冲宽度受限于最大结温。
- 2. $I_{AS} = 8.3 \text{ A}$, $R_G = 25 \Omega$, 启动 $T_J = 25^{\circ}\text{C}$ 。
 3. $I_{SD} \le 25 \text{ A}$, di/dt $\le 200 \text{ A/}\mu\text{s}$, $V_{DD} \le 380 \text{ V}$, 启动 $T_J = 25^{\circ}\text{C}$ 。
- 4. 本质上独立于工作温度的典型特性。

典型性能特征

图 1. 导通区域特性

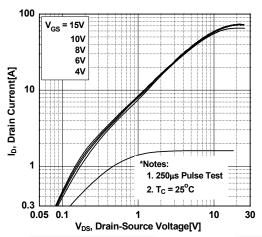


图 3. 导通电阻变化与漏极电流和栅极电压

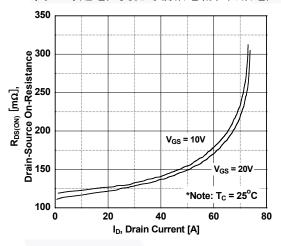


图 5. 电容特性

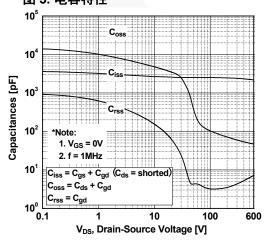


图 2. 传输特性

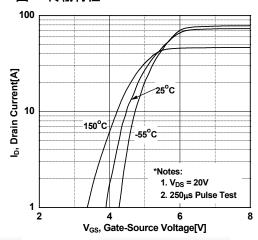


图 4. 体二极管正向电压变化与源极电流和温度

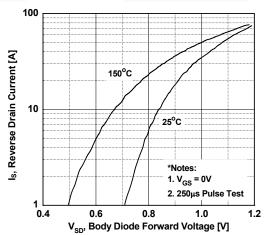
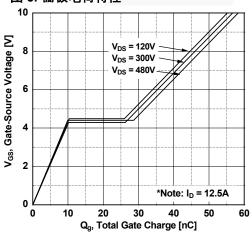


图 6. 栅极电荷特性



典型性能特征 (接上页)

图 7. 击穿电压变化与温度

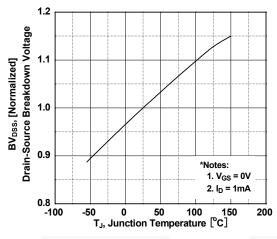


图 8. 导通电阻变化与温度

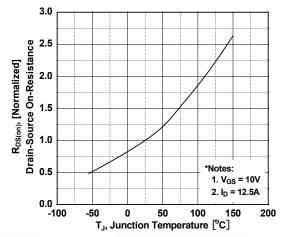


图 9. 最大安全工作区

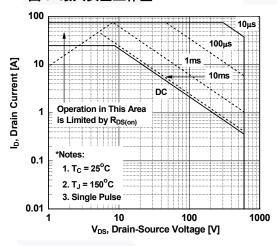


图10. 最大漏极电流与外壳温度

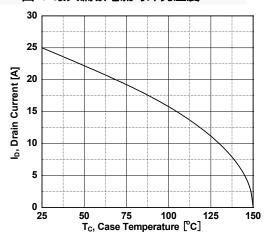
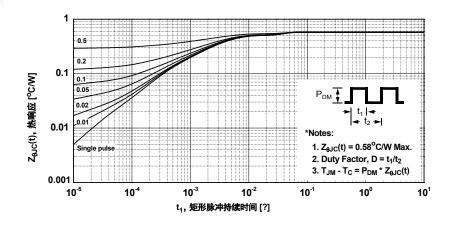


图 11. 瞬态热响应曲线



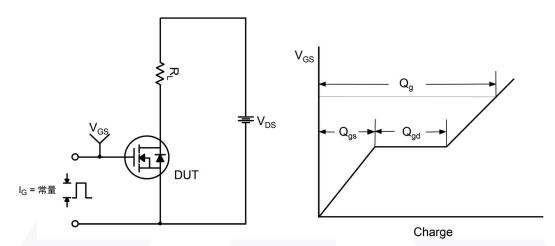


图 12. 栅极电荷测试电路与波形

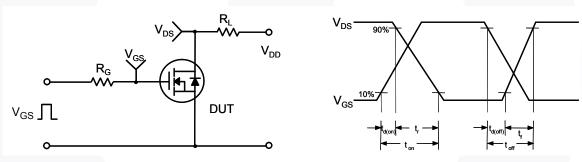


图 13. 阻性开关测试电路与波形

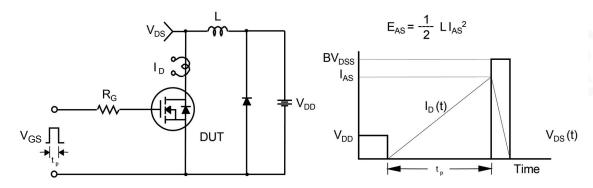


图 14. 非箝位感性开关测试电路与波形

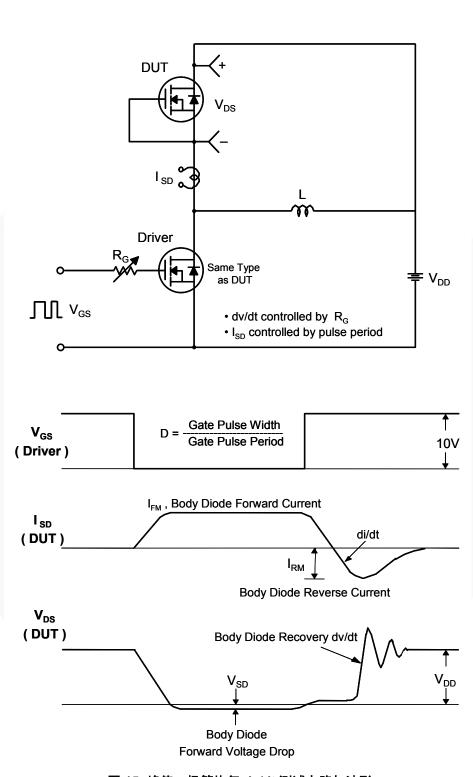
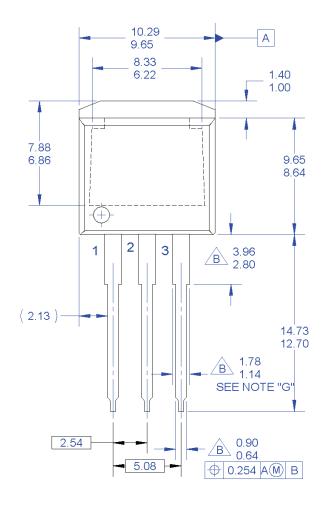
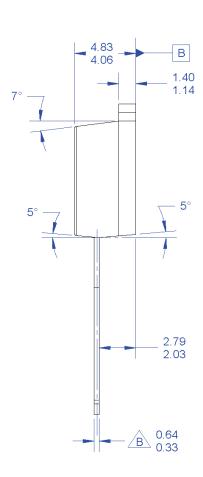


图 15. 峰值二极管恢复 dv/dt 测试电路与波形

机械尺寸





NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO
 TO262 JEDEC VARIATION AA.

 B. DOES NOT COMPLY JEDEC STD. VALUE.
 C. ALL DIMENSIONS ARE IN MILLIMETERS.
 D. DIMENSIONS ARE EXCLUSIVE OF BURRS,
 MOLD FLASH AND TIE BAR PROTRUSIONS.
 E. DIMENSION AND TOLERANCE AS PER ANSI
 VAL 5 1904
- Y14.5-1994.
- F. LOCATION OF PIN HOLE MAY VARY
 (LOWER LEFT CORNER, LOWER CENTER
 AND CENTER OF PACKAGE)
 G. MAXIMUM WIDTH FOR F102 DEVICE = 1.35 MAX.
 H. DRAWING FILE NAME: TO262A03REV5

图 16. TO262 (I²PAK),模塑, 3 引脚, Jedec 变体 AA

封装图纸作为一项服务,提供给考虑飞兆半导体元件的客户。具体参数可能会有变化,且不会做出相应通知。请注意图纸上的版本和 / 或日期,并联系飞兆半导体代表核实或获得最新版本。封装规格并不扩大飞兆公司全球范围内的条款与条件,尤其是其中涉及飞兆公司 产品保修的部分。

随时访问飞兆半导体在线封装网页,可以获取最新的封装图纸:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN TT262-0I3





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ AX-CAP® BitSiC™ Build it Now™ CorePLUS™ CorePOWER™ $CROSSVOLT^{\text{TM}}$

CTI ™ Current Transfer Logic™ DEUXPEED® Dual Cool™ EcoSPARK®

EfficentMax™ ESBC™

Fairchild[®] Fairchild Semiconductor® FACT Quiet Series™ FACT® FAST® FastvCore™ FETBench™ FPS™

F-PFS™ FRFET® Global Power ResourceSM

GreenBridge™ Green FPS™ Green FPS™ e-Series™

G*max*™ GTO™ IntelliMAX™ ISOPLANAR™

Marking Small Speakers Sound Louder

and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ MillerDrive™

MotionMax™ mWSaver® OptoHiT™ OPTOLOGIC® OPTOPLANAR® PowerTrench® PowerXS™

Programmable Active Droop™

QFET QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SvncFET™

Sync-Lock™ SYSTEM ®* TinyBoost[®] TinyBuck[®] TinyCalc™ TinyLogic[®] TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TranSiC™

TriFault Detect™

μSerDes™

TRUECURRENT®*

UHC[®] Ultra FRFET™ UniFFT™ VCX™ VisualMax™ VoltagePlus™

XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE
EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information Formative / In Design		Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed Full Production		Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete Not In Production		Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev 166

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative